

METHOD OF PROCESSING WAFER AND PROCESSING APPARATUS FOR WAFER

ABSTRACT

A method of processing a wafer to divide the wafer into individual device chips, includes a second modified layer forming step of applying a laser beam to the wafer while positioning a focused spot of the laser beam inside the wafer along the projected dicing lines extending in a second direction intersecting with a first direction, thereby forming second modified layers in the wafer along the projected dicing lines extending in the second direction. In the second modified layer forming step, when the focused spot of the laser beam applied to the wafer along the projected dicing lines extending in the second direction reaches first modified layers, the focused spot of the laser beam is shifted along the first modified layers to thereby undulate the laser beam in a staggered pattern to prevent the second modified layers from being formed straight in the wafer along the projected dicing lines extending in the second direction.

[Fig. 3]